UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

NOTICE OF ALLOWANCE AND FEE(S) DUE

25224

APPLICATION NO.

7590

12/30/2009

MORRISON & FOERSTER, LLP 555 WEST FIFTH STREET SUITE 3500 LOS ANGELES, CA 90013-1024 EXAMINER

COLEMAN, RYAN L

ART UNIT PAPER NUMBER

1792

DATE MAILED: 12/30/2009

FILING DATE FIRST NAMED INVENTOR ATTORNEY DOCKET NO. CONFIRMATION NO.

10/579,423 05/11/2006 Takayuki Toshima 514312000400 1339

TITLE OF INVENTION: SUBSTRATE PROCESSING METHOD, SUBSTRATE PROCESSING APPARATUS AND COMPUTER-READABLE MEMORY MEDIUM

APPLN. TYPE	SMALL ENTITY	ISSUE FEE DUE	PUBLICATION FEE DUE	PREV. PAID ISSUE FEE	TOTAL FEE(S) DUE	DATE DUE
nonprovisional	NO	\$1510	\$300	\$0	\$1810	03/30/2010

THE APPLICATION IDENTIFIED ABOVE HAS BEEN EXAMINED AND IS ALLOWED FOR ISSUANCE AS A PATENT. PROSECUTION ON THE MERITS IS CLOSED. THIS NOTICE OF ALLOWANCE IS NOT A GRANT OF PATENT RIGHTS. THIS APPLICATION IS SUBJECT TO WITHDRAWAL FROM ISSUE AT THE INITIATIVE OF THE OFFICE OR UPON PETITION BY THE APPLICANT. SEE 37 CFR 1.313 AND MPEP 1308.

THE ISSUE FEE AND PUBLICATION FEE (IF REQUIRED) MUST BE PAID WITHIN THREE MONTHS FROM THE MAILING DATE OF THIS NOTICE OR THIS APPLICATION SHALL BE REGARDED AS ABANDONED. THIS STATUTORY PERIOD CANNOT BE EXTENDED. SEE 35 U.S.C. 151. THE ISSUE FEE DUE INDICATED ABOVE DOES NOT REFLECT A CREDIT FOR ANY PREVIOUSLY PAID ISSUE FEE IN THIS APPLICATION. IF AN ISSUE FEE HAS PREVIOUSLY BEEN PAID IN THIS APPLICATION (AS SHOWN ABOVE), THE RETURN OF PART B OF THIS FORM WILL BE CONSIDERED A REQUEST TO REAPPLY THE PREVIOUSLY PAID ISSUE FEE TOWARD THE ISSUE FEE NOW DUE.

HOW TO REPLY TO THIS NOTICE:

I. Review the SMALL ENTITY status shown above.

If the SMALL ENTITY is shown as YES, verify your current SMALL ENTITY status:

A. If the status is the same, pay the TOTAL FEE(S) DUE shown above

B. If the status above is to be removed, check box 5b on Part B - Fee(s) Transmittal and pay the PUBLICATION FEE (if required) and twice the amount of the ISSUE FEE shown above, or

If the SMALL ENTITY is shown as NO:

A. Pay TOTAL FEE(S) DUE shown above, or

B. If applicant claimed SMALL ENTITY status before, or is now claiming SMALL ENTITY status, check box 5a on Part B - Fee(s) Transmittal and pay the PUBLICATION FEE (if required) and 1/2 the ISSUE FEE shown above.

II. PART B - FEE(S) TRANSMITTAL, or its equivalent, must be completed and returned to the United States Patent and Trademark Office (USPTO) with your ISSUE FEE and PUBLICATION FEE (if required). If you are charging the fee(s) to your deposit account, section "4b" of Part B - Fee(s) Transmittal should be completed and an extra copy of the form should be submitted. If an equivalent of Part B is filed, a request to reapply a previously paid issue fee must be clearly made, and delays in processing may occur due to the difficulty in recognizing the paper as an equivalent of Part B.

III. All communications regarding this application must give the application number. Please direct all communications prior to issuance to Mail Stop ISSUE FEE unless advised to the contrary.

IMPORTANT REMINDER: Utility patents issuing on applications filed on or after Dec. 12, 1980 may require payment of maintenance fees. It is patentee's responsibility to ensure timely payment of maintenance fees when due.

PART B - FEE(S) TRANSMITTAL

Complete and send this form, together with applicable fee(s), to: Mail Mail Stop ISSUE FEE

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

or <u>Fax</u> (571)-273-2885

INSTRUCTIONS: This form should be used for transmitting the ISSUE FEE and PUBLICATION FEE (if required). Blocks 1 through 5 should be completed where m

appropriate. All further indicated unless correcte maintenance fee notifica	correspondence includir ed below or directed oth tions.	ng the Patent, advance on nerwise in Block 1, by (a	rders and notification of n a) specifying a new corres	naintenance fees w pondence address;	/ill be : and/or	mailed to the current (b) indicating a sepa	correspondence address a arate "FEE ADDRESS" fo	
CURRENT CORRESPONDENCE ADDRESS (Note: Use Block 1 for any change of address)				Note: A certificate of mailing can only be used for domestic mailings of the Fee(s) Transmittal. This certificate cannot be used for any other accompanying papers. Each additional paper, such as an assignment or formal drawing, mus have its own certificate of mailing or transmission.				
25224	7590 12/30	/2009	nave			· ·	mission	
555 WEST FIFT SUITE 3500		.P	I he State addr trans	Certificate of Mailing or Transm I hereby certify that this Fee(s) Transmittal is being States Postal Service with sufficient postage for first addressed to the Mail Stop ISSUE FEE address a transmitted to the USPTO (571) 273-2885, on the dat			deposited with the United t class mail in an envelope above, or being facsimile tte indicated below.	
LOS ANGELES	S, CA 90013-1024						(Depositor's name	
							(Signature	
							(Date	
APPLICATION NO.	FILING DATE		FIRST NAMED INVENTOR		ATTO:	RNEY DOCKET NO.	CONFIRMATION NO.	
10/579,423	05/11/2006	•	Takayuki Toshima		4	514312000400	1339	
TITLE OF INVENTION MEMORY MEDIUM	N: SUBSTRATE PRO	OCESSING METHOD,	SUBSTRATE PROCESS	ING APPARATU	JS AN	D COMPUTER-REA	ADABLE	
APPLN. TYPE	SMALL ENTITY	ISSUE FEE DUE	PUBLICATION FEE DUE	PREV. PAID ISSUI	E FEE	TOTAL FEE(S) DUE	DATE DUE	
nonprovisional	NO	\$1510	\$300	\$0		\$1810	03/30/2010	
EXAM	IINER	ART UNIT	CLASS-SUBCLASS					
COLEMAN	N, RYAN L	1792	134-001000					
 Change of correspondence address or indication of "Fee Address" (37 CFR 1.363). Change of correspondence address (or Change of Correspondence Address form PTO/SB/122) attached. "Fee Address" indication (or "Fee Address" Indication form PTO/SB/47; Rev 03-02 or more recent) attached. Use of a Customer Number is required. 			or agents OR, alternative (2) the name of a single registered attorney or a	mes of up to 3 registered patent attorneys OR, alternatively, me of a single firm (having as a member a attorney or agent) and the names of up to ade patent attorneys or agents. If no name is				
PLEASE NOTE: Unl recordation as set fort (A) NAME OF ASSIG	less an assignee is ident h in 37 CFR 3.11. Comp GNEE	ified below, no assignee oletion of this form is NO	THE PATENT (print or type data will appear on the part a substitute for filing an (B) RESIDENCE: (CITY	atent. If an assignassignment. and STATE OR C	COUNT	RY)		
Please check the appropr	iate assignee category or	categories (will not be pr	rinted on the patent): \Box	Individual 🖵 Co	orporati	on or other private gro	oup entity 🖵 Governmen	
4a. The following fee(s) are submitted: ☐ Issue Fee ☐ Publication Fee (No small entity discount permitted) ☐ Advance Order - # of Copies			b. Payment of Fee(s): (Plea A check is enclosed. Payment by credit car The Director is hereby overpayment, to Depo	d. Form PTO-2038	is atta	ched. required fee(s), any de		
	s SMALL ENTITY statu	is. See 37 CFR 1.27.	☐ b. Applicant is no long	-				
NOTE: The Issue Fee an interest as shown by the	d Publication Fee (if requeecords of the United Sta	uired) will not be accepte tes Patent and Trademark	d from anyone other than the Office.	ne applicant; a regi	stered a	nttorney or agent; or th	ne assignee or other party i	
Authorized Signature				Date				
Typed or printed name								
This collection of inform an application. Confiden submitting the complete this form and/or suggesti Box 1450, Alexandria, V Alexandria Virginia 223	tiality is governed by 35 d application form to the ions for reducing this but rirginia 22313-1450. DC	FR 1.311. The informatic U.S.C. 122 and 37 CFR USPTO. Time will vary rden, should be sent to th ONOT SEND FEES OR	on is required to obtain or r 1.14. This collection is est depending upon the indiv e Chief Information Office COMPLETED FORMS TO	etain a benefit by t imated to take 12 r idual case. Any co r, U.S. Patent and D THIS ADDRESS	he publ minutes mment Traden S. SENI	ic which is to file (and to complete, including s on the amount of the nark Office, U.S. Dep D TO: Commissioner	d by the USPTO to process ng gathering, preparing, an me you require to complet artment of Commerce, P.G for Patents, P.O. Box 1450	

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.



United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/579,423	05/11/2006	Takayuki Toshima	514312000400	1339	
25224 75	590 12/30/2009		EXAMINER		
MORRISON & I	FOERSTER, LLP	COLEMAN, RYAN L			
555 WEST FIFTH	STREET	ART UNIT	PAPER NUMBER		
SUITE 3500 LOS ANGELES, 0	CA 90013-1024		1792 DATE MAILED: 12/30/200	9	

Determination of Patent Term Adjustment under 35 U.S.C. 154 (b)

(application filed on or after May 29, 2000)

The Patent Term Adjustment to date is 798 day(s). If the issue fee is paid on the date that is three months after the mailing date of this notice and the patent issues on the Tuesday before the date that is 28 weeks (six and a half months) after the mailing date of this notice, the Patent Term Adjustment will be 798 day(s).

If a Continued Prosecution Application (CPA) was filed in the above-identified application, the filing date that determines Patent Term Adjustment is the filing date of the most recent CPA.

Applicant will be able to obtain more detailed information by accessing the Patent Application Information Retrieval (PAIR) WEB site (http://pair.uspto.gov).

Any questions regarding the Patent Term Extension or Adjustment determination should be directed to the Office of Patent Legal Administration at (571)-272-7702. Questions relating to issue and publication fee payments should be directed to the Customer Service Center of the Office of Patent Publication at 1-(888)-786-0101 (571)-272-4200.

	Application No.	Applicant(s)	
Notice of Allowability	10/579,423 Examiner	TOSHIMA ET AL. Art Unit	
•			
	RYAN COLEMAN	1792	
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIOF the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate commu IGHTS. This application is s	this application. If not included inication will be mailed in due course. THI	
1. X This communication is responsive to applicant's amendment	nts filed October 16, 2009.		
2. X The allowed claim(s) is/are <u>1-5,7-14,16-21,29,30,32 and 3</u>	<u>4</u> .		
 3. Acknowledgment is made of a claim for foreign priority ur a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 	, , ,	or (f).	
2. Certified copies of the priority documents have	been received in Application	n No	
Copies of the certified copies of the priority do	cuments have been received	d in this national stage application from the	е
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received:			
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		a reply complying with the requirements	
4. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give			
5. CORRECTED DRAWINGS (as "replacement sheets") mus	st be submitted.		
(a) ☐ including changes required by the Notice of Draftspers	on's Patent Drawing Reviev	v (PTO-948) attached	
1) 🔲 hereto or 2) 🔲 to Paper No./Mail Date			
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	s Amendment / Comment or	in the Office action of	
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t			
 DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT 			
Attachment(s)	5 □ Notice of In	Formal Detant Application	
 Notice of References Cited (PTO-892) D Notice of Draftperson's Patent Drawing Review (PTO-948) 		formal Patent Application ummary (PTO-413),	
,	Paper No./	Mail Date	
 Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date <u>May 11, 2006</u> 	7. 🛛 Examiner's	Amendment/Comment	
4. Examiner's Comment Regarding Requirement for Deposit	8. 🛛 Examiner's	Statement of Reasons for Allowance	
of Biological Material	9. 🔲 Other	<u>.</u>	
/RLC/	/Michael Barr/		
Ryan L. Coleman	Supervisory Pat	ent Examiner, Art Unit 1792	
Examiner 12/18/09			

Art Unit: 1792

DETAILED ACTION

Election/Restrictions

1. Applicant's election without traverse of Group I, claims 1-21 and 29-36, in the reply filed on October 16, 2009 is acknowledged. Applicant withdrew claims 22-28 in the same reply.

EXAMINER'S AMENDMENT

- 2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.
- 3. Authorization for this examiner's amendment was given in a telephone interview with David Kim on December 16, 2009.
- 4. Replace claim 1 with the following:

A substrate processing method for removing an ArF resist film from a substrate having the ArF resist film, comprising the steps of:

irradiating an ultraviolet ray having a predetermined wavelength to the ArF resist film;

altering the ArF resist film irradiated with the ultraviolet ray into a water-soluble state by placing the substrate in a chamber and feeding an ozone gas and water vapor to the chamber; and

Art Unit: 1792

removing the ArF resist film from the substrate by feeding pure water to the ArF resist film altered into the water soluble state[[.]].

wherein when the water vapor and the ozone gas are fed to the chamber, a feed amount of ozone gas with respect to the water vapor is decreased while the water vapor is fed to said chamber at a constant flow rate in such a way as not to cause dew condensation on the substrate placed in the chamber.

5. Replace claim 3 with the following:

A substrate processing method for removing an antireflection film from a substrate having said antireflection film, comprising the steps of:

irradiating an ultraviolet ray having a predetermined wavelength to the antireflection film;

altering the antireflection film irradiated with the ultraviolet ray into a watersoluble state by placing the substrate in a chamber and feeding an ozone gas and water vapor to the chamber; and

removing said antireflection film from the substrate by feeding pure water to said reflection film altered into the water-soluble state[[.]],

wherein when the water vapor and the ozone gas are fed to the chamber, a feed amount of ozone gas with respect to the water vapor is decreased while the water vapor is fed to said chamber at a constant flow rate in such a way as not to cause dew condensation on the substrate placed in the chamber.

6. Replace claim 4 with the following:

A substrate processing method for removing a resist film from a substrate having the resist film undergone an ion implantation process at a high dose, comprising the steps of:

irradiating an ultraviolet ray having a predetermined wavelength to said resist film;

altering the resist film irradiated with the ultraviolet ray into a water-soluble state by placing the substrate in a chamber and feeding an ozone gas and water vapor to the chamber; and

removing the resist film from the substrate by feeding pure water to the resist film altered into the water soluble state[[.]].

wherein when the water vapor and the ozone gas are fed to the chamber, a feed amount of ozone gas with respect to the water vapor is decreased while the water vapor is fed to said chamber at a constant flow rate in such a way as not to cause dew condensation on the substrate placed in the chamber.

7. Replace claim 10 with the following:

A substrate processing method for removing an ArF resist film from a substrate having the ArF resist film, comprising the steps of:

irradiating an ultraviolet ray having a predetermined wavelength to the ArF resist film;

altering said ArF resist film irradiated with the ultraviolet ray in a such a way as to be water-soluble with a predetermined chemical solution by placing the substrate in a chamber and feeding an ozone gas and water vapor to the chamber; and

Art Unit: 1792

removing the ArF resist film from the substrate by feeding the chemical liquid to the altered ArF resist film[[.]].

wherein when the water vapor and the ozone gas are fed to the chamber, a feed amount of ozone gas with respect to the water vapor is decreased while the water vapor is fed to the chamber at a constant flow rate in such a way as not to cause dew condensation on the substrate placed in the chamber.

8. Replace claim 12 with the following:

A substrate processing method for removing an antireflection film from a substrate having the antireflection film, comprising the steps of:

irradiating an ultraviolet ray having a predetermined wavelength to the antireflection film;

altering said antireflection film irradiated with the ultraviolet ray in a such a way as to be soluble with a predetermined chemical liquid by placing the substrate in a chamber and feeding an ozone gas and water vapor to the chamber; and

removing the antireflection film from the substrate by feeding the chemical liquid to the altered antireflection film[[.]].

wherein when the water vapor and the ozone gas are fed to the chamber, a feed amount of ozone gas with respect to the water vapor is decreased while the water vapor is fed to the chamber at a constant flow rate in such a way as not to cause dew condensation on the substrate placed in the chamber.

9. Replace claim 13 with the following:

Art Unit: 1792

A substrate processing method for removing a resist film from a substrate having the resist film undergone an ion implantation process at a high dose, comprising the steps of:

irradiating an ultraviolet ray having a predetermined wavelength to the resist film; altering the resist film irradiated with the ultraviolet ray in a such a way as to be soluble with a predetermined chemical liquid by placing said substrate in a chamber and feeding an ozone gas and water vapor to the chamber; and

removing the resist film from the substrate by feeding the chemical liquid to the altered resist film[[.]].

wherein when the water vapor and the ozone gas are fed to the chamber, a feed amount of ozone gas with respect to the water vapor is decreased while the water vapor is fed to the chamber at a constant flow rate in such a way as not to cause dew condensation on the substrate placed in the chamber.

- 10. In claims 7 and 8, replace the number "6" with the number "1".
- 11. In claims 16 and 17, replace the number "15" with the number "10".
- 12. In claim 32, replace the number "31" with the number "3".
- 13. In claim 34, replace the number "33" with the number "4".
- 14. Cancel claims 6, 15, 22-28, 31, 33, 35, and 36.

Art Unit: 1792

Reasons for Allowance

15. The following is an examiner's statement of reasons for allowance: the reviewed prior are does not teach or render obvious the inventions specified in the independent claims.

16. The most relevant prior art is U.S. Patent Application Publication No. 2002/0185225 by Toshima et al. (hereafter referred to as "Toshima '225"), U.S. Patent No. 6,616,773 to Kuzumoto et al. (hereafter referred to as "Kuzumoto"), and U.S. Patent No. 6,613,692 to Toshima et al. (hereafter referred to as "Toshima '692"). Toshima '225 teaches a method of removing ArF resist film from a substrate that comprises altering the ArF resist film into a water-soluble state by placing the substrate in a chamber and feeding ozone gas and water vapor into the chamber (Par. 0035, 0036, and 0093-0097). Toshima '225 teaches removing the altered resist film from the substrate by feeding rinse fluid to the altered film (Par. 0097). Kuzumoto teaches that it is advantageous to irradiate a resist layer with ultraviolet light of a predetermined wavelength prior to performing a resist-removal treatment with ozone gas and water vapor (Col. 20, 39-62). Toshima '692 teaches that a method of removing resist with ozone and water vapor can also remove an antireflective layer positioned beneath the resist layer (Col. 7, line 25 to Col. 8, line 52; Col. 38, 41-50). However, the prior art fails to teach or suggest the concept of decreasing a feed amount of ozone gas with respect to water vapor flowing into the chamber at a constant flow rate in such a way as not to cause dew condensation on the treated substrate.

Art Unit: 1792

17. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

- 18. Any inquiry concerning this communication or earlier communications from the examiner should be directed to RYAN COLEMAN whose telephone number is (571)270-7376. The examiner can normally be reached on Monday-Friday, 9-5.
- 19. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Kornakov can be reached on (571)272-1303. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.
- 20. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Art Unit: 1792

/RLC/ Ryan L. Coleman Patent Examiner, Art Unit 1792 December 18, 2009 /Michael Barr/ Supervisory Patent Examiner, Art Unit 1792